

軍商兩用貨品及技術出口管制清單及一般軍用貨品清單

新、舊版修正對照與翻譯

編列說明

1. 軍商兩用貨品及技術出口管制清單列入第一項，一般軍用貨品清單列入第二項。
2. 本對照表列出下列情況：
 - a. 中文有增/刪語詞，原意有所變動者；
 - b. 舊版無、新版新增之內容；
 - c. 舊版有、新版刪除之內容；
3. 本對照表未列出下列情況，但已於檔案中進行修正，與現行公布英文版本一致：
 - a. 標點符號變動、專有名詞單引號或雙引號變動、CAS 編號前加註 CAS 字樣者；
 - b. 英文編輯改變，未改變原有內容意義者；
 - c. 排版方式變更，未改變原有內容意義者；
 - d. 既有版本的錯字與誤植。
4. 為符合國際文體指南(2015 年版)，英文版本以逗號分隔整數與小數，以空間分隔表明千位整數。

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第一項：軍商兩用貨品及技術出口管制清單修正對照表

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
字首集合字 與縮寫	無	定義用詞之字首集合字與縮寫，請參見“本附件中使用的術語定義”。(P4)	-	For acronyms and abbreviations used as defined terms, see ‘Definitions of Terms used in this Annex’.
字首集合字 與縮寫	無	ECAD Electronic Computer-Aided Design 電子計算機輔助設計	-	ECAD Electronic Computer-Aided Design
字首集合字 與縮寫	無	GAAFET Gate-All-Around Field-Effect Transistor 環繞式閘極場效電晶體	-	GAAFET Gate-All-Around Field-Effect Transistor
專用術語定義	“單晶微波積體電路”(“MMIC”)(第3、5類)指“單晶積體電路”以微波或毫米波進行運作。	無修正	"Monolithic Microwave Integrated Circuit" ("MMIC") (3 5) means a "monolithic integrated circuit" that operates at microwave or millimeter wave frequencies.	"Monolithic Microwave Integrated Circuit" ("MMIC") (3 5) means a "monolithic integrated circuit" that operates at microwave or millimetre wave frequencies.
	“超合金”(第2、9類)指鎳基、鈷基或鐵基合金，其在壓力400 MPa、溫度922 K (649 °C)或超過情況下，斷裂應力壽命大於1,000 小時者。	“超級合金”(第2、9類)是指鎳基、鈷基或鐵基合金，其在400 MPa 下的斷裂應力壽命大於1,000 小時，且在922 K (649 °C)下或更高情況下的極限抗拉強度大於850 MPa 者。(P22)	"Superalloys" (2 9) means nickel-, cobalt- or iron-base alloys having a stress rupture life greater than 1 000 hours at 400 MPa at 922 K (649 °C) or higher.	"Superalloys" (2 9) means nickel-, cobalt- or iron-base alloys having a stress rupture life greater than 1 000 hours at 400 MPa and an ultimate tensile strength greater than 850 MPa, at 922 K (649 °C) or higher.
專用術語定義	無	“環繞式閘極場效電晶體”(“GAAFET”) 一種具有單個或多個半導體傳導通道元件的裝置，該裝置具有圍繞並控制所有半導體傳導通道元件中的電流的公共閘極結構。 註解 此定義包括奈米片或奈米線場效應和周圍閘極晶體管和其他“GAAFET”	-	"Gate-All-Around Field-Effect Transistor" ("GAAFET") A device having a single or multiple semiconductor conduction channel element(s) with a common gate structure that surrounds and controls current in all of the semiconductor conduction channel elements. Note This definition includes nanosheet or nanowire field-effect and surrounding gate transistors and other "GAAFET" semiconductor channel element

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		半導體通道元件結構。		structures.
1C007 Technical Note	e. 特別設計之「前驅材料」，用以生產 1C007.c.所述，如下： 1. 聚二有機矽烷； 2. 聚矽氮烷； 3. 聚碳矽氮烷； 技術註解： 1C007 所述之「前驅材料」，指特殊用途聚合物或金屬有機材料，其用於「生產」碳化矽、氮化矽或具有矽、碳及氮成分之陶瓷。 f. 刪除；	e. 特別設計之「前驅材料」，用以生產 1C007.c.所述，如下： 1. 聚二有機矽烷； 2. 聚矽氮烷； 3. 聚碳矽氮烷； f. 刪除； 技術註解： 1C007 所述之「前驅材料」，指特殊用途聚合物或金屬有機材料，其用於「生產」碳化矽、氮化矽或具有矽、碳及氮成分之陶瓷。(P58)	e. 'Precursor materials' specially designed for the "production" of materials specified in 1C007.c., as follows: 1.Polydiorganosilanes; 2.Polysilazanes; 3.Polycarbosilazanes; Technical Note: For the purposes of 1C007, 'precursor materials' are special purpose polymeric or metallo-organic materials used for the "production" of silicon carbide, silicon nitride, or ceramics with silicon, carbon and nitrogen. f. Not used.	e. 'Precursor materials' specially designed for the "production" of materials specified in 1C007.c., as follows: 1.Polydiorganosilanes; 2.Polysilazanes; 3.Polycarbosilazanes; f. Not used. Technical Note: For the purposes of 1C007, 'precursor materials' are special purpose polymeric or metallo-organic materials used for the "production" of silicon carbide, silicon nitride, or ceramics with silicon, carbon and nitrogen.
1C117.c.1.c.	c. 以重量百分比計算鎢含量比率達 80 % 或以上之銀鎢合金；及	無修正	c. Silver infiltrated tungsten containing 80 % by weight of more of tungsten; and	c. Silver infiltrated tungsten containing 80 % by weight or more of tungsten; and
2B006.b.1	1. 在 0 至 0.2 mm「量測範圍」之中，「解析度」等於或小於(優於)0.2 μm 之「非接觸式測量系統」； 技術註解： 就 2B006.b.1.所述： 1.「非接觸式測量系統」，其設計用於測量探針或被測量物在運動時，兩者沿著單一向量之間的距離； 2.「量測範圍」指最小與最大工作距離之間的距離。	1. 在 0 至 0.2 mm「量測範圍」之中，「解析度」等於或小於(優於)0.2 μm 之「非接觸式測量系統」； 技術註解： 就 2B006.b.1.所述： 1.「非接觸式測量系統」，其設計用於測量探針或被測量物在運動時，兩者沿著單一向量之間的距離； 2.「量測範圍」指最小與最大工作距離之間的距離。(P99)	1. 'Non-contact type measuring systems' with a "resolution" equal to or less (better) than 0,2 μm within a measuring range up to 0,2 mm; Technical Note: For the purposes of 2B006.b.1. 'non-contact type measuring systems' are designed to measure the distance between the probe and measured object along a single vector, where the probe or measured object is in motion.	1. 'Non-contact type measuring systems' with a resolution equal to or less (better) than 0,2 μm within a measuring range up to 0,2 mm; Technical Note: For the purposes of 2B006.b.1. 'non-contact type measuring systems' are designed to measure the distance between the probe and measured object along a single vector, where the probe or measured object is in motion.
2B006.b.3.b.	b. 整個量測範圍內之「解析度」為 0.2 nm 或以下(優於)；及	b. 整個量測範圍內之「解析度」為 0.2 nm 或以下(優於)；及(P99)	b. A "resolution" over their full scale of 0,200 nm or less (better); and	b. A resolution over their full scale of 0,200 nm or less (better); and
2B206.c.2.a.	a. 「解析度」在全尺度情況下等於或	a. 「解析度」在全尺度情況下等於或優	a. A "resolution" over their full scale of 0,1 μm or better; and	a. A resolution over their full scale of 0,1 μm or better; and

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	優於 0,1 µm；及	於 0,1 µm；及(P106)		
2B230.a.	a. 壓力感測元件以鋁、鋁合金、氧化鋁(礬土或藍寶石)、鎳、含鎳重量百分比超過 60 %之鎳合金，或全氟化烴聚合物製造或保護；及	無修正	a. Pressure sensing elements made of or protected by aluminium, aluminium alloy, aluminum oxide (alumina or sapphire), nickel, nickel alloy with more than 60 % nickel by weight, or fully fluorinated hydrocarbon polymers;	a. Pressure sensing elements made of or protected by aluminium, aluminium alloy, aluminium oxide (alumina or sapphire), nickel, nickel alloy with more than 60 % nickel by weight, or fully fluorinated hydrocarbon polymers;
2B230.b.	b. 密封件，其必須使用密封性壓力感測元件，且與處理之介質直接接觸，以鋁、鋁合金、氧化鋁(礬土或藍寶石)、鎳、含鎳重量百分比超過 60%之鎳合金，或全氟化烴聚合物製造或保護者；及	無修正	b. Seals, if any, essential for sealing the pressure sensing element, and in direct contact with the process medium, made of or protected by aluminium, aluminium alloy, aluminum oxide (alumina or sapphire), nickel, nickel alloy with more than 60 % nickel by weight, or fully fluorinated hydrocarbon polymers; and	b. Seals, if any, essential for sealing the pressure sensing element, and in direct contact with the process medium, made of or protected by aluminium, aluminium alloy, aluminium oxide (alumina or sapphire), nickel, nickel alloy with more than 60 % nickel by weight, or fully fluorinated hydrocarbon polymers; and
2B352.f.2. Note 2	註解 2：2B352.f.2.不管制特別為護理、運輸感染患者而設計之隔離器。	註解 2：管制具上述所有特性之隔離器，無論其預期用途或名稱為何。 註解 3：2B352.f.2.不管制特別為護理、運輸感染患者而設計之隔離器。(P118)	Note 2: 2B352.f.2. does not include isolators specially designed for barrier nursing or transportation of infected patients.	Note 2: includes any isolator meeting all of the above- mentioned characteristics, regardless of its intended use and its designation. Note 3: 2B352.f.2. does not include isolators specially designed for barrier nursing or transportation of infected patients.
2D001.a.	a. 為“開發”或“生產” 2A001 或 2B001 所述之設備而特別設計或修改之“軟體”。	a. 為“開發”或“生產” 2A001 或 2B001 至 2B009 所述之設備而特別設計或修改之“軟體”。(P118)	a. "Software" specially designed or modified for the "development" or "production" of equipment specified in 2A001 or 2B001.	a. "Software" specially designed or modified for the "development" or "production" of equipment specified in 2A001 or 2B001 to 2B009.
3A001.a.	技術註解： 1. n 位元之解析度係對應於一個量子	無修正	Technical Notes: 1. A resolution of n bit corresponds to a quantisation of 2n levels.	Technical Note: 1. A resolution of n bit corresponds to a quantisation of 2n levels.

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	<p>化的 2n 種狀態。</p> <p>2. 輸出字的位元數相等於數位一類比轉換器之解析度，有效位元數 (ENOB) 不用於判讀 ADC 之解析度。</p> <p>3. 對於「多頻道 ADCs」而言，「取樣率」非為匯總結果，且「取樣率」是指任何單一頻道之最大輸出率。</p> <p>4. 對於「交錯式 ADCs」或「多頻道 ADCs」而言，「取樣率」為匯總結果，「取樣率」為所有交錯頻道之最大輸出率組合。</p>		<p>2. The resolution of the ADC is the number of bits of the digital output that represents the measured analogue input. Effective Number of Bits (ENOB) is not used to determine the resolution of the ADC.</p> <p>3. For "multiple channel ADCs", the "sample rate" is not aggregated and the "sample rate" is the maximum rate of any single channel.</p> <p>4. For "interleaved ADCs" or for "multiple channel ADCs" that are specified to have an interleaved mode of operation, the "sample rates" are aggregated and the "sample rate" is the maximum combined total rate of all of the interleaved channels.</p>	<p>2. The resolution of the ADC is the number of bits of the digital output that represents the measured analogue input. Effective Number of Bits (ENOB) is not used to determine the resolution of the ADC.</p> <p>3. For "multiple channel ADCs", the "sample rate" is not aggregated and the "sample rate" is the maximum rate of any single channel.</p> <p>4. For "interleaved ADCs" or for "multiple channel ADCs" that are specified to have an interleaved mode of operation, the "sample rates" are aggregated and the "sample rate" is the maximum combined total rate of all of the interleaved channels.</p>
3A228.a. (Note)	註解：3A228 所述包括充氣弧光放電管及真空放電管。	註解：3A228.a. 所述包括充氣弧光放電管及真空放電管。(P156)	Note: 3A228 includes gas krytron tubes and vacuum sprytron tubes.	Note: 3A228.a. includes gas krytron tubes and vacuum sprytron tubes.
3C005.a	a. 碳化矽晶圓(SiC)、氮化鎵(GaN)、氮化鋁(AlN)或氮化鋁鎵(AlGaIn)之半導體「基板」，或錠、圓柱狀、其它型態之上述材料，在 20 °C 時電阻率大於 10,000 ohm-cm 者	a. 碳化矽晶圓(SiC)、氮化鎵(GaN)、氮化鋁(AlN)、氮化鋁鎵(AlGaIn)、氧化鎵(Ga ₂ O ₃)或鑽石之半導體「基板」，或錠、圓柱狀、其它型態之上述材料，在 20 °C 時電阻率大於 10,000 ohm-cm 者	a. Silicon carbide (SiC), gallium nitride (GaN), aluminium nitride (AlN) or aluminium gallium nitride (AlGaIn) semiconductor "substrates", or ingots, boules, or other preforms of those materials, having resistivities greater than 10 000 ohm-cm at 20 °C;	a. Silicon carbide (SiC), gallium nitride (GaN), aluminium nitride (AlN), aluminium gallium nitride (AlGaIn), gallium oxide (Ga ₂ O ₃) or diamond semiconductor "substrates", or ingots, boules, or other preforms of those materials, having resistivities greater than 10,000 ohm-cm at 20°C;
3C005.b	b. 多晶「基板」或多晶陶瓷「基板」，在 20 °C 時電阻率大於 10,000 ohm-cm，且「基板」表面具至少一層矽(Si)、碳化矽晶圓(SiC)、氮化鎵(GaN)、氮化鋁(AlN)或氮化鋁鎵	b. 多晶「基板」或多晶陶瓷「基板」，在 20 °C 時電阻率大於 10,000 ohm-cm，且「基板」表面具至少一層矽(Si)、碳化矽晶圓(SiC)、氮化鎵(GaN)、氮化鋁(AlN)、氮化鋁鎵	b. Polycrystalline "substrates" or polycrystalline ceramic "substrates", having resistivities greater than 10 000 ohm-cm at 20 °C and having at least one non-epitaxial single-crystal layer of silicon (Si), silicon carbide	b. Polycrystalline "substrates" or polycrystalline ceramic "substrates", having resistivities greater than 10,000 ohm-cm at 20°C and having at least one non-epitaxial single-crystal layer of silicon (Si), silicon carbide (SiC),

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	(AlGaIn)的非外延單晶層。	(AlGaIn)、氧化鎵(Ga ₂ O ₃)或鑽石的非外延單晶層。	(SiC), gallium nitride (GaN), aluminium nitride (AlN), or aluminium gallium nitride (AlGaIn) on the surface of the "substrate".	gallium nitride (GaN), aluminium nitride (AlN), aluminium gallium nitride (AlGaIn), gallium oxide (Ga ₂ O ₃) or diamond on the surface of the "substrate".
3C006	未在 3C001 中所述之材料，含有 3C005 所述“基板”，至少有一個磊晶層為碳化矽，氮化鎵，氮化鋁或氮化鋁鎵。	未在 3C001 中所述之材料，含有 3C005 所述“基板”，至少有一個磊晶層為碳化矽，氮化鎵，氮化鋁、氮化鋁鎵、氧化鎵(Ga ₂ O ₃)或鑽石。	Materials, not specified in 3C001, consisting of a "substrate" specified in 3C005 with at least one epitaxial layer of silicon carbide, gallium nitride, aluminium nitride or aluminium gallium nitride.	Materials, not specified by 3C001, consisting of a "substrate" specified by 3C005. with at least one epitaxial layer of silicon carbide, gallium nitride, aluminium nitride, aluminium gallium nitride, gallium oxide (Ga ₂ O ₃) or diamond.
3D006	無	<p>“電子計算機輔助設計”(“ECAD”) “軟體”專為“開發”具有任何“環繞式閘極場效電晶體”(“GAAFET”)結構的積體電路而設計，並且具有任何下列的：</p> <p>a.專為將“暫存器轉移層次”(“RTL”)實施到“幾何數據庫標準 II”(“GDSII”)或同等標準而設計；或</p> <p>b.專為優化功率或時序規則而設計。</p> <p>技術註解</p> <p>1. “電子計算機輔助設計”(“ECAD”)是一類“軟體”工具，用於設計、分析、優化和驗證積體電路或印刷電路板的性能。</p> <p>2. “暫存器轉移層次”(“RTL”)是一種設計抽象模型，它根據硬體暫存器之間的數位訊號以及對這些訊號執行的邏輯操作來模擬同步數位電路。</p> <p>3. “幾何數據庫標準 II”</p>	-	<p>'Electronic Computer-Aided Design' ('ECAD') "software" specially designed for the "development" of integrated circuits having any "Gate-All-Around Field-Effect Transistor" ("GAAFET") structure, and having any of the following:</p> <p>a.Specially designed for implementing 'Register Transfer Level' ('RTL') to 'Geometrical Database Standard II' ('GDSII') or equivalent standard; or</p> <p>b.Specially designed for optimisation of power or timing rules.</p> <p>Technical Notes</p> <p>1.'Electronic Computer-Aided Design' ('ECAD') is a category of "software" tools used for designing, analysing, optimising, and validating the performance of integrated circuit or</p>

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		(“GDSII”)是一種用於積體電路或積體電路佈局圖數據交換的數據庫文件格式。		printed circuit board. 2.'Register Transfer Level' ('RTL') is a design abstraction which models a synchronous digital circuit in terms of the flow of digital signals between hardware registers, and the logical operations performed on those signals. 3.'Geometrical Database Standard II' ('GDSII') is a database file format for data exchange of integrated circuit or integrated circuit layout artwork.
3E003.d	d. 用於電子零件之鑽石薄膜基板	d. 用於電子零件之鑽石基板	d. Substrates of films of diamond for electronic components.	d. Substrates of diamond for electronic components;
5A004.b. (Note 2)	註解：5A004.b.不包括： a. 除錯器、虛擬化管理程序； b. 僅限於邏輯資料提取的項目； c. 利用晶片分離(chip-off)或 JTAG 進行資料提取的項目；或 d. 特別設計限制越獄(jail-breaking)或獲得作業系統超級使用者權限(rooting)的項目。	註解 2：5A004.b.不包括： a. 除錯器、虛擬化管理程序； b. 僅限於邏輯資料提取的項目； c. 利用晶片分離(chip-off)或 JTAG 進行資料提取的項目；或 d. 特別設計限制越獄(jail-breaking)或獲得作業系統超級使用者權限(rooting)的項目。(P191)	Note: 5A004.b. does not include: a. Debuggers, hypervisors; b. Items limited to logical data extraction; c. Data extraction items using chip-off or JTAG; or d. Items specially designed and limited to jail-breaking or rooting.	Note 2: 5A004.b. does not include: a. Debuggers, hypervisors; b. Items limited to logical data extraction; c. Data extraction items using chip-off or JTAG; or d. Items specially designed and limited to jail-breaking or rooting.
9A001 (Note 1.b.2.)	2. 經 ICAO(國際民航組織)認可之等效文件。	無修正	2. An equivalent document recognized by the International Civil Aviation Organisation (ICAO).	2. An equivalent document recognised by the International Civil Aviation Organization (ICAO).
9E003.a.2.e	無	e.利用“壓力增益燃燒”； 技術註解 當發動機以“穩態模式”運行時，在“壓力增益燃燒”的燃燒過程中，其燃燒器出口處的整體平均停滯壓力大於燃燒器入口處的整體平均停滯壓	-	e.Utilising 'pressure gain combustion'; Technical Note In 'pressure gain combustion' the bulk average stagnation pressure at the combustor outlet is greater than the bulk average stagnation pressure at the combustor inlet due primarily to

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		力。		the combustion process, when the engine is running in a "steady state mode" of operation.

第二項：一般軍用貨品清單修正對照表

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
ML1., Note d.	d. 停用槍械。	d. 停用槍械。 技術註解： 「停用槍械」是指通過瓦聖那協議參與國的國家當局規定的程序之無法發射任何射彈的槍支。這些程序不可逆轉地改變了槍支的基本要素。根據國家法律法規，槍支的停用可以由主管當局出具的證書證明，並可以在槍支的重要部分加蓋印章。(P295)	d. "Deactivated firearms".	d. 'Deactivated firearms'. Technical Note A 'deactivated firearm' is a firearm that has been made incapable of firing any projectile by processes defined by the Wassenaar Arrangement Participating State's national authority. These processes irreversibly modify the essential elements of the firearm. According to national laws and regulations, deactivation of the firearm may be attested by a certificate delivered by a competent authority and may be marked on the firearm by a stamp on an essential part.
ML1.d.3.	3. 特殊槍架；	3. 槍架； 技術註解： 就 ML1.d.3. 而言，“槍架”是設計用於將槍安裝到地面車輛、“飛行器”、船隻或結構上的固定裝置。(P296)	3. Special gun-mountings;	3. 'Gun-mountings'; Technical Note For the purposes of ML1.d.3., a 'gun-mounting' is a fixture designed to mount a gun onto a ground vehicle, "aircraft", vessel or structure.
ML10.f.	f. 特別為 ML10.a.所述之“航空器”或 ML10.d.所述之航空發動機而開發之地面設備； 技術註解： 「地面設備」包括增壓加油設備與設計用於狹窄區域操作之設備。	f. 特別為 ML10.a.所述之“航空器”或 ML10.d.所述之航空發動機而開發之地面設備； 註解： ML10.f. 包括壓力加油設備和設計用於在促進在狹窄區域作業的設備，包括船上的設備。(P321)	f. 'Ground equipment' specially designed for "aircraft" specified by ML10.a. or aero-engines specified by ML10.d.; Technical Note 'Ground equipment' includes pressure refuelling equipment and equipment designed to facilitate	f. Ground equipment specially designed for "aircraft" specified by ML10.a. or aero-engines specified by ML10.d.; Note ML10.f. includes pressure refuelling equipment and equipment designed to facilitate operations in confined areas,

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
			operations in confined areas.	including equipment located on board a ship.
ML13	c. 根據軍事標準或規格，或相當的國家標準製作之頭盔，及為其特別設計之頭盔外殼、內襯或舒適墊；說明：其他軍用頭盔零件或配件，參照 ML 相關之條目。	c. 頭盔及其專門設計的部件和附件，如下： 1. 根據軍事標準或規格，或以等同國家標準所製作的頭盔； 2. 專為 ML13.c.1 規範之頭盔設計的外殼、內襯或舒適墊； 3. 附加防彈保護元件，專為 ML13.c.1 中規範之頭盔設計。 說明：對於其他軍用頭盔組件或配件，請參閱相關 ML 條目。(P324)	c. Helmets manufactured according to military standards or specifications, or comparable national standards, and specially designed helmet shells, liners, or comfort pads, therefor; N.B. For other military helmet components or accessories, see the relevant Common Military List entry	c. Helmets and specially designed components and accessories therefor, as follows: 1. Helmets manufactured according to military standards or specifications, or comparable national standards; 2. Shells, liners, or comfort pads, specially designed for helmets specified in ML13.c.1.; 3. Add-on ballistic protection elements, specially designed for helmets specified in ML13.c.1. N.B. For other military helmet components or accessories, see the relevant ML entry.
ML13., Note 2	註解 2：ML13.c.不管制傳統鋼盔係為未經改裝或設計，且無加裝任何形式之配件裝置。	註解 2：ML13.c.不管制以下所有條件的頭盔： a. 在 1970 年之前首次製造；和 b. 未經改裝或設計，且無加裝任何彈藥清單內列管品項。(P324)	Note 2 ML13.c. does not apply to conventional steel helmets, neither modified or designed to accept, nor equipped with any type of accessory device.	Note 2 ML13.c. does not apply to helmets that meet all of the following: a. Were first manufactured before 1970; and b. Are neither designed or modified to accept, nor equipped with items specified by the Munitions List.
ML18.b.	b. 為一般軍用貨品清單所管制貨品之認證、合格鑑定或測試而特別設計之環境測試設施及其特別設計之設備。	b. 其他地方未明確律定，係專為一般軍用貨品清單所管制貨品進行認證、合格鑑定或測試，而特別設計之環境測試設施及其特別設計之設備。(P327)	b. Specially designed environmental test facilities and specially designed equipment therefor, for the certification, qualification or testing of products specified by the Common Military List.	b. Specially designed environmental test facilities and specially designed equipment therefor, not specified elsewhere , for the certification, qualification or testing of products specified by the Munitions List.